



JPW

Docket No.: 61352-075

**PATENT**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of	:	Customer Number: 20277
	:	
Nobuyuki OTSUKA, et al.	:	Confirmation Number: 2226
	:	
Serial No.: 10/817,035	:	Group Art Unit: 2811
	:	
Filed: April 05, 2004	:	Examiner: Not Yet Assigned
	:	
For:	:	A GALLIUM INDIUM NITRIDE ARSENIDE BASED EPITAXIAL WAFER, A HETERO FIELD EFFECT TRANSISTOR USING THE WAFER, AND A METHOD OF FABRICATING THE HETERO FIELD EFFECT TRANSISTOR

**INFORMATION DISCLOSURE STATEMENT**

Mail Stop IDS  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached form PTO-1449. It is respectfully requested that the references be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

10/817,035

Each non-English language reference was first cited in a corresponding foreign application search report or office action and its relevance discussed therein. A copy of the international search report is attached for the Examiner's information

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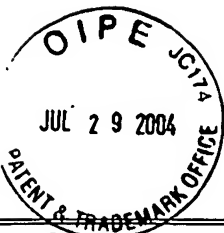
Respectfully submitted,

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**Date: July 29, 2004**



SHEET 1 OF 1

<b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b>  <b>(PTO-1449)</b>				ATTY. DOCKET NO. <b>61352-075</b>		SERIAL NO. <b>10/817,035</b>	
				APPLICANT <b>Nobuyuki OTSUKA, et al.</b>			
				FILING DATE <b>April 05, 2004</b>		GROUP <b>2811</b>	
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
		US					
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<b>FOREIGN PATENT DOCUMENTS</b>							
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes -Number -Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No
		JP 2003-289082 A	10-10-2002	MATSUSHITA ELECTRIC IND CO LTD		JAPAN (w/English Abstract)	
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<b>OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.					
		HANG, D.R. et al., "Shubnikov-de Haas oscillations of two-dimensional electron gas in and in AsN/InGaAs single quantum well", <i>Semiconductor Science and Technology</i> , Vol. 17, no. 9, September 2002, pp. 999-1003					
		WANG, Jyh-Shyang et al., "Growth of InAsn/InGaAs (P) quantum wells on InP by gas source molecular beam epitaxy", <i>Journal of Vacuum Science &amp; Technology B</i> , Vol. 19, No. 1 January/February 2001, pp 202-206					
EXAMINER				DATE CONSIDERED			

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.  
 1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.